NL17SZ17

Single Non-Inverting Buffer with Schmitt Trigger

The NL17SZ17 is a single Non−inverting Schmitt Trigger Buffer in two tiny footprint packages. The device performs much as LCX multi−gate products in speed and drive.

Features

- Tiny SOT−353 and SOT−553 Packages
- Source/Sink 24 mA at 3.0 Volts
- Overvoltage Tolerant Inputs and Outputs
- Chip Complexity: FETs = 20
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Pb−Free Packages are Available

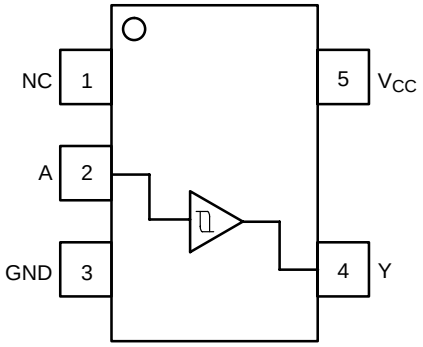

Figure 1. Pinout (Top View)

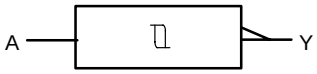

Figure 2. Logic Symbol

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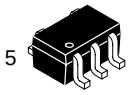
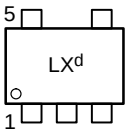
MARKING DIAGRAMS

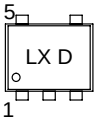


SOT−353/SC70−5/SC−88A
DF SUFFIX
CASE 419A



d = Date Code

SOT−553
XV5 SUFFIX
CASE 463B



LX = Device Marking
D = One Digit Date Code

PIN ASSIGNMENT

Pin	Function
1	NC
2	A
3	GND
4	Y
5	V_{CC}

FUNCTION TABLE

A Input	Y Output
L	L
H	H

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +7.0$	V
V_O	DC Output Voltage	Output in High or LOW State (Note 1)	$-0.5 \le V_O \le 7.0$	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOT−353 (Note 2) SOT−553	350 496	°C/W
P_D	Power Dissipation in Still Air at 85°C	SOT−353 SOT−553	186 135	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 6)	±500	mA
ESD	ESD Classification	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model	Class IC Class A N/A	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
3. Tested to EIA/JESD22−A114−A, rated to EIA/JESD22−A114−B.
4. Tested to EIA/JESD22−A115−A, rated to EIA/JESD22−A115−A.
5. Tested to JESD22−C101−A.
6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage, (Note 7)		0	5.5	V
V_O	Output Voltage	(HIGH or LOW State)	0	5.5	V
T_A	Operating Free−Air Temperature		−40	+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ±0.2 V V_{CC} = 3.0 V ±0.3 V V_{CC} = 5.0 V ±0.5 V	0 0 0	No Limit No Limit No Limit	ns/V

7. Unused inputs may not be left open. All inputs must be tied to a high−logic voltage level or a low−logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
V_T+	Positive Input Threshold Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.6 1.0 1.2 1.3 1.9 2.2	1.0 1.5 1.7 1.9 2.7 3.3	1.4 1.8 2.0 2.2 3.1 3.6	0.6 1.0 1.2 1.3 1.9 2.2	1.4 1.8 2.0 2.2 3.1 3.6	V
V_T-	Negative Input Threshold Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.2 0.4 0.5 0.6 1.0 1.2	0.5 0.75 0.87 1.0 1.5 1.9	0.8 1.15 1.4 1.5 2.0 2.3	0.2 0.4 0.5 0.6 1.0 1.2	0.8 1.15 1.4 1.5 2.0 2.3	V
V_H	Input Hysteresis Voltage		1.65 2.3 2.7 3.0 4.5 5.5	0.1 0.25 0.3 0.4 0.6 0.7	0.48 0.75 0.83 0.93 1.2 1.4	0.9 1.1 1.15 1.2 1.5 1.7	0.1 0.25 0.3 0.4 0.6 0.7	0.9 1.1 1.15 1.2 1.5 1.7	V
V_{OH}	High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA I_{OH} = −3 mA I_{OH} = −8 mA I_{OH} = −12 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V_{CC} −0.1 1.29 1.9 2.2 2.4 2.3 3.8	V_{CC} 1.52 2.1 2.4 2.7 2.5 4.0		V_{CC} −0.1 1.29 1.9 2.2 2.4 2.3 3.8		V
V_{OL}	Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA I_{OL} = 4 mA I_{OL} = 8 mA I_{OL} = 12 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I_{OFF}	Power Off−Output Leakage Current	V_{OUT} = 5.5 V	0			1.0		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			1.0		10	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Input A to Y (Figures 3 and 4)	R_L = 1 MΩ, C_L = 15 pF	1.65 1.8 2.5 ± 0.2 3.3 ± 0.3 5.0 ± 0.5	2.0 2.0 1.0 1.0 0.5	9.1 7.6 5.0 3.7 3.1	15 12.5 9.0 6.3 5.2	2.0 2.0 1.0 1.0 0.5	15.6 13 9.5 6.5 5.5	ns
		R_L = 500 Ω, C_L = 50 pF	3.3 ± 0.3 5.0 ± 0.5	1.5 0.8	4.4 3.7	7.2 5.9	1.5 0.8	7.5 6.2	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	>2.5	pF
C_{PD}	Power Dissipation Capacitance (Note 8)	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	9 11	pF

8. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

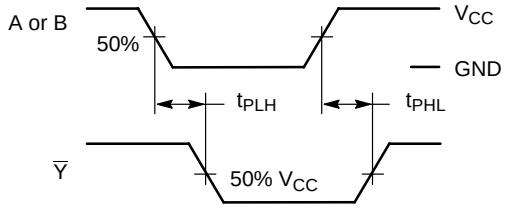
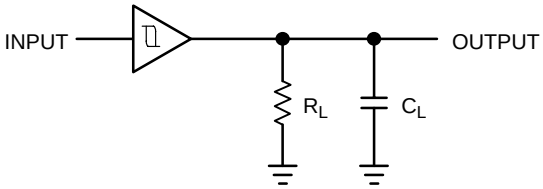


Figure 3. Switching Waveforms



A 1 MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

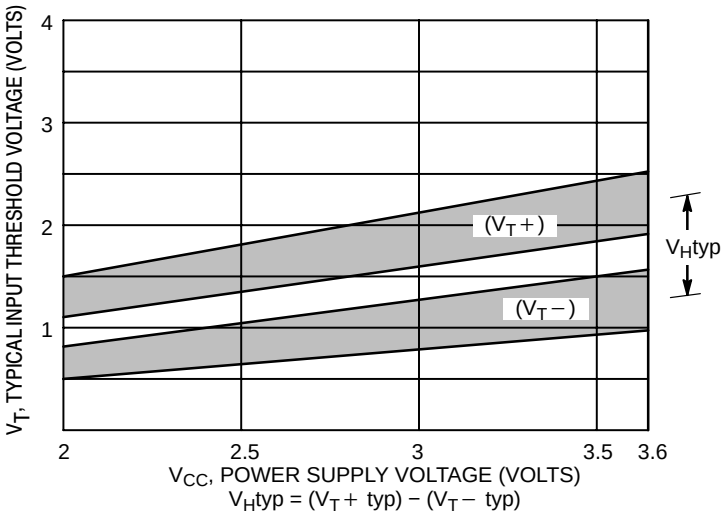
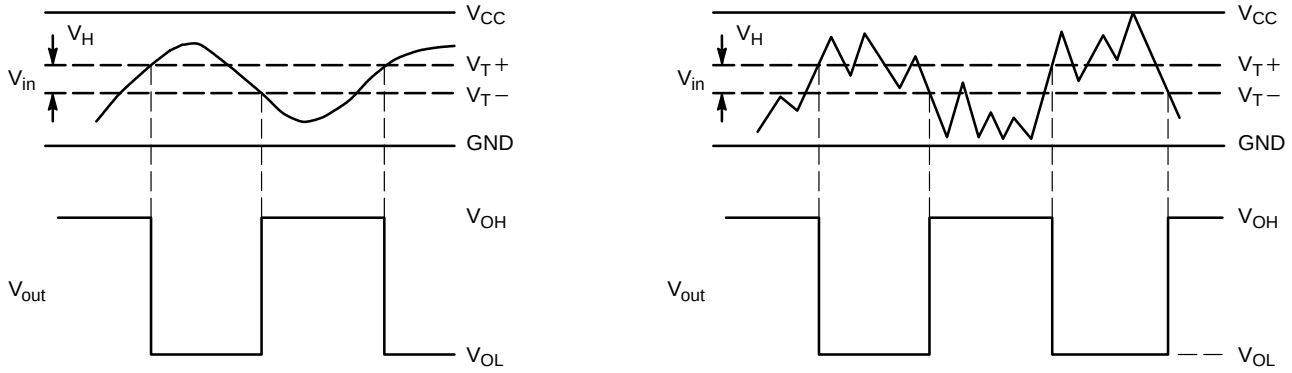


Figure 5. Typical Input Threshold, V_T+, V_T- versus Power Supply Voltage



(a) A Schmitt−Trigger Squares Up Inputs With Slow Rise and Fall Times

(b) A Schmitt−Trigger Offers Maximum Noise Immunity

Figure 6. Typical Schmitt−Trigger Applications

DEVICE ORDERING INFORMATION

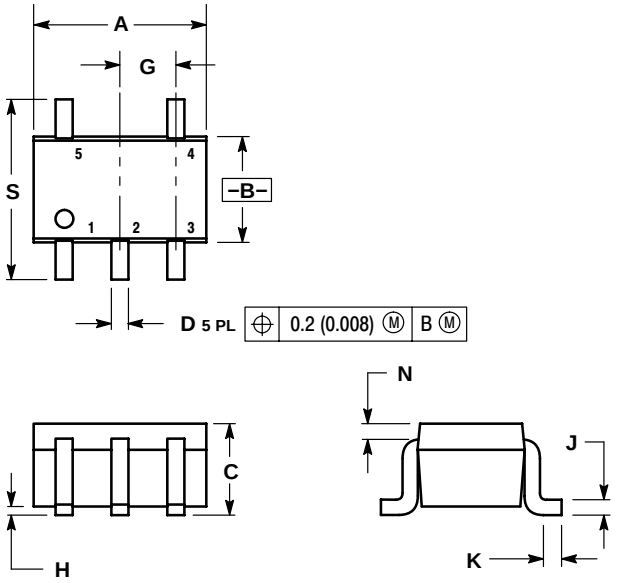
Device Order Number	Device Nomenclature							Package Type	Tape/Reel Size†
	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix		
NL17SZ17DFT2	NL	1	7	SZ	17	DF	T2	SOT−353/SC70−5/ SC−88A	178 mm, 3000 Units
NL17SZ17DFT2G	NL	1	7	SZ	17	DF	T2	SOT−353/SC70−5/ SC−88A (Pb−Free)	178 mm, 3000 Units
NL17SZ17XV5T2	NL	1	7	SZ	17	XV5	T2	SOT−553* (Pb−Free)	178 mm, 4000 Units

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb−Free.

PACKAGE DIMENSIONS

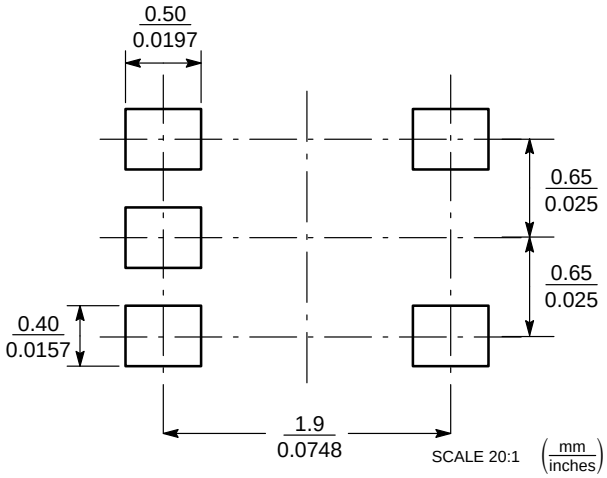
SOT−353
DF SUFFIX
5−LEAD PACKAGE
CASE 419A−02
ISSUE G



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

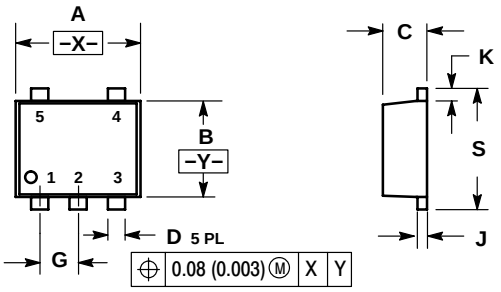
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT−553
XV5 SUFFIX
5−LEAD PACKAGE
CASE 463B−01
ISSUE A



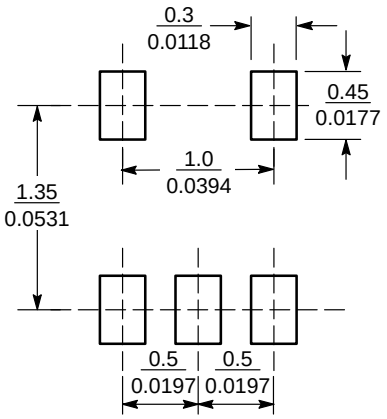
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	1.10	1.30	0.043	0.051
C	0.50	0.60	0.020	0.024
D	0.17	0.27	0.007	0.011
G	0.50 BSC		0.020 BSC	
J	0.08	0.18	0.003	0.007
K	0.10	0.30	0.004	0.012
S	1.50	1.70	0.059	0.067

STYLE 1:
PIN 1. BASE 1
2. EMITTER 1/2
3. BASE 2
4. COLLECTOR 2
5. COLLECTOR 1

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

NL17SZ17/D